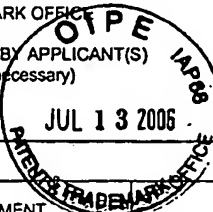



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		APPLICANT  <b>KAZUYA NOTSU, ET AL.</b>					
		FILING DATE  <b>Not Yet Assigned</b>		GROUP <b>2815</b> <b>Not Yet Assigned</b>			
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO 1448 (modified)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)				ATTY DOCKET NO. <b>00862.102568.</b>		APPLICATION NO. <b>10/540,261</b>	
				APPLICANT <b>KAZUYA NOTSU, ET AL.</b>			
				FILING DATE <b>10/540,261</b>		GROUP <b>2815</b>	
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EXAMINER				DATE CONSIDERED <b>10/06</b>			

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